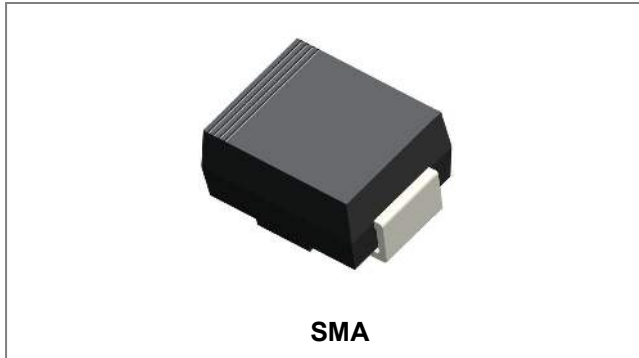


## ES2A-ES2J SURFACE MOUNT SUPER FAST RECTIFIER



### Features

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Overload Drop, High Efficiency
- Low Power Loss
- Super-Fast Recovery Time
- Plastic Case Material has UL Flammability Classification Rating 94V-O
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Circuit Diagram



### Mechanical Data

- Case: Low Profile Molded Plastic
- Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026
- Polarity: Cathode Band or Cathode Notch
- Marking: Type Number
- Weight: 0.06 grams(approx)

### Maximum Ratings and Electrical Characteristics @ $T_A=25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	ES2A	ES2B	ES2C	ES2D	ES2E	ES2G	ES2J	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	50	100	150	200	300	400	600	V
RMS Reverse Voltage	$V_{R(RMS)}$	34	70	105	140	210	280	420	
Average Rectified Output Current @ $T_L = 110^\circ\text{C}$	$I_O$	2.0							A
Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	$I_{FSM}$	50							A
Forward Voltage @ $I_F = 2.0\text{A}$ , $T_J = 25^\circ\text{C}$	$V_F$	0.95			1.25		1.7		V
Maximum DC reverse current at rated DC blocking voltage	$I_R$				5.0 500				$\mu\text{A}$
Typical junction capacitance (Note 1)	$C_J$				25				pF
Maximum Reverse Recovery Time (Note 2)	$T_{rr}$				35				ns
Typical thermal resistance (Note 3)	$R_{\theta JL}$				20				K/W
Operating junction and storage temperature range	$T_J, T_{STG}$				-55 to +150				$^\circ\text{C}$

**Note:** 1. Measured at 1.0 MHz and applied reverse voltage of 4.0 V<sub>DC</sub>  
 2. Measured with  $I_F=0.5\text{A}$ ,  $I_R=1.0\text{A}$ ,  $I_{rr}=0.25\text{A}$   
 3. Mounted on P.C. Board with 8.0mm<sup>2</sup> lead area

**Ratings and Characteristics Curves**

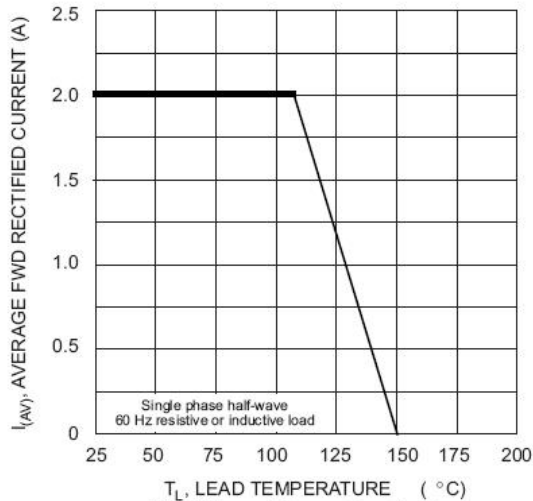


Fig. 1 Forward Current Derating Curve

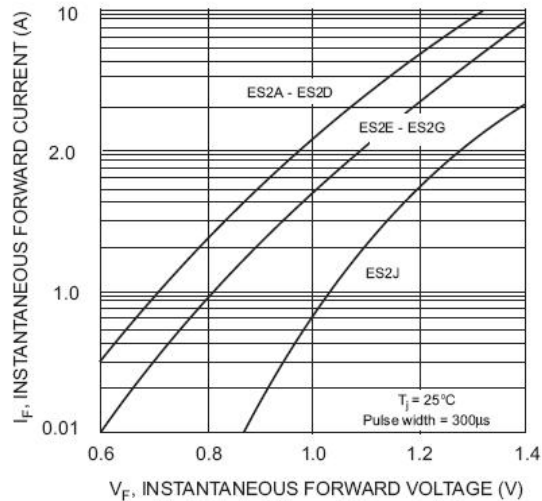


Fig. 2 Typical Forward Characteristics

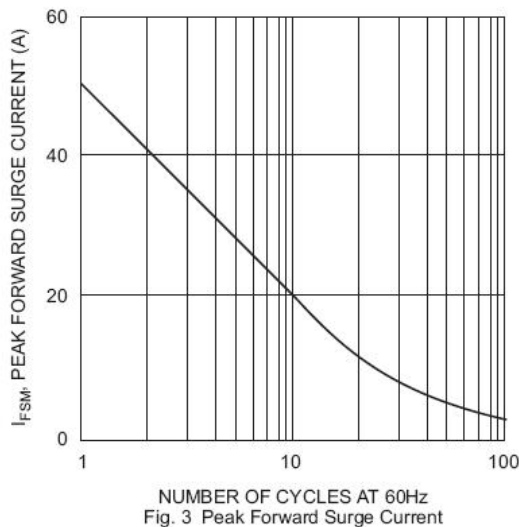


Fig. 3 Peak Forward Surge Current

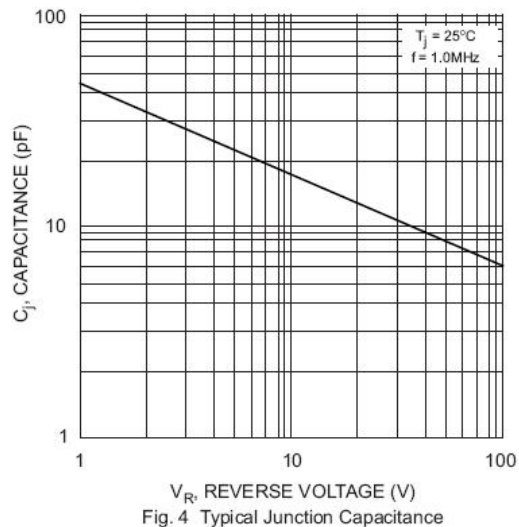
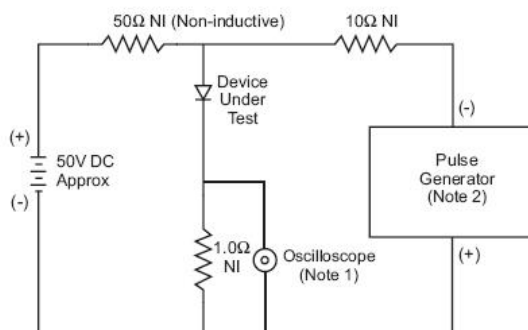


Fig. 4 Typical Junction Capacitance



Notes:  
1. Rise Time = 7.0ns max. Input Impedance = 1.0M $\Omega$ , 22pF.  
2. Rise Time = 10ns max. Input Impedance = 50 $\Omega$ .

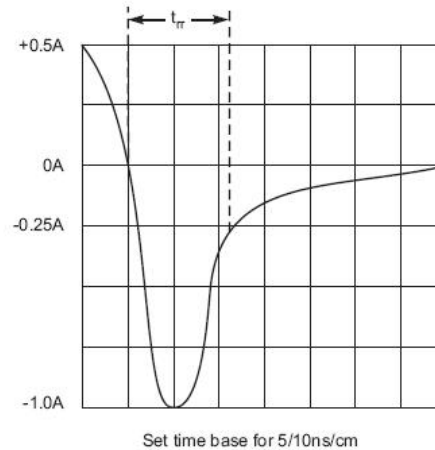
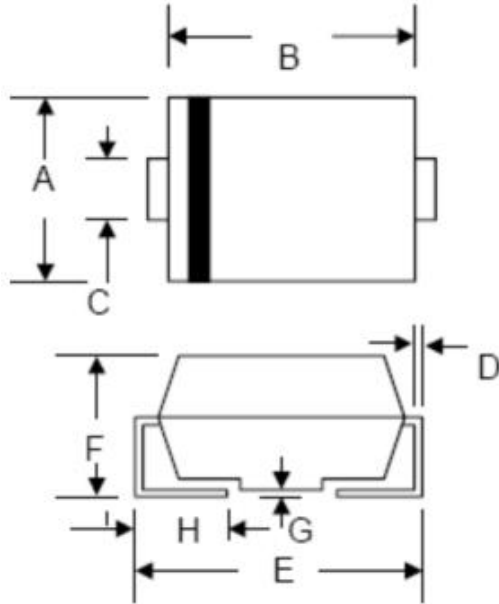


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

**Mechanical Dimensions SMA**



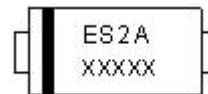
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	2.18	2.90	0.086	0.114
B	3.99	4.60	0.157	0.181
C	1.29	1.70	0.508	0.067
D	0.152	0.305	0.006	0.012
E	4.70	5.31	0.185	0.209
F	1.70	2.50	0.067	0.098
G	0.051	0.203	0.002	0.008
H	0.76	1.55	0.030	0.610

**Ordering Information**

Device	Package	Shipping
ES2A-ES2M	SMA (Pb-Free)	5000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**

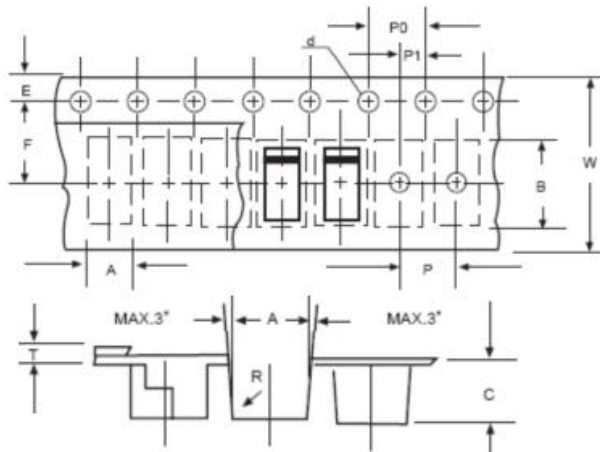


Where XXXXX is YYWWL

- ES = Device Type
- 2 = Forward Current (2A)
- A = Reverse Voltage (50V)
- YY = Year
- WW = Week
- L = Lot Number

**Cautions:** Molding resin  
Epoxy resin UL:94V-0

**Carrier Tape Specification SMA**



SYMBOL	Millimeters	
	Min.	Max.
A	2.97	3.17
B	5.70	5.90
C	2.32	2.52
d	1.40	1.60
E	1.40	1.60
F	5.60	5.70
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
T	0.25	0.35
W	11.80	12.20

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